

University of Oviedo

Laser and Plasma Spectroscopy Research Group www.unioviedo.es/gelp



# Magnetically Boosted Glow Discharge Optical Emission Spectroscopy for Analytical Applications: Pros and Cons

J. Pisonero, N. Bordel



Rf-GD-OES is an analytical technique widely used for material characterization in different techological fields



Rf-GD-OES is an analytical technique widely used for material characterization in different techological fields ✓ Fast and sensitive multielemental analysis for solid materials ✓ Low matrix effects (separated atomization and excitation/ionization processes)

✓ High depth resolution (~nm)



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Due to the magnetic and electric field combination (defined by the Lorentz Force) the plasma electron paths are modified.

$$\vec{F} = q \cdot \left( \vec{E} + \vec{v} \times \vec{B} \right)$$

$$\vec{E} \downarrow \stackrel{\vec{v}\uparrow}{=} \stackrel{\vec{v}f}{=} \stackrel{\vec{v}f}{=} \vec{F}_{E}$$

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- $\blacktriangleright$  Electrons are more effectively confined than ions by the magnetic field R<sub>e</sub> is aprox. 300 lower than R<sub>i</sub>
- Ions are not affected by the presence of the magnetic field R<sub>i</sub> is higher that the size of the plasma
- > The higher the magnetic field the lower the radius

The electron residence time on the GD plasma is enlarged and collision probability is increased.

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Excitation/ionization efficiencies, plasma distribution, transport processes....may be affected.

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	Emission intensities	
Effect of the magnetic field on -	Depth resolution	
	Sputtering rates	
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GD TYPE	MAGNETIC FIELD	EMISSION LINES	ENHANCEMENT FACTOR	REFERENCE
Hollow cathode	50 mT on magnet surface (plasma site)	Mg I – 285.2 nm	up to 3	Raghani <i>et al</i> . <i>Appl. Spectrosc.,</i> 1996, <b>50</b> , 417
Hollow cathode	100 mT on cathode axis (plasma site)	Cu I – 324.7 nm	up to 4	Simonneau <i>et al.</i> <i>Appl. Spectrosc.,</i> 1989, <b>43</b> , 141
Planar cathode 60 mT on cathode surface (sample backside)	60 mT on cathode surface	Cu I – 406.2 nm	up to 7	Mc.Caig et al.
	(sample backside)	Al I – 396.2 nm	up to 7	Appl. Spectrosc., 1990, <b>44</b> , 1176
	Planar cathode 30 mT on cathode surface (plasma site)	Cu I – 324.7 nm	up to 1.3	Chen <i>et al</i> . SAB 1997, <b>52</b> , 1161
Planar cathode 30		Al I – 396.2 nm	up to 1.5	
		Ni I – 341.5 nm	up to 1.8	
Grimm	10 mT on cathode surface (sample backside)	Al I – 396.2 nm	up to 1.5	Alberts <i>et al</i> . JAAS, 2010, <b>25</b> , 1247
Grimm	32 mT on cathode surface (sample backside)	Cu I – 282.4 nm	up to 2	Heintz <i>et al</i> . Appl. Spectrosc., 1995, <b>49</b> , 241

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Dlanar oothodo	60 mT on cat		up to 7	Mc.Caig et al.
Planar cathode	(sample b		up to 7	Appl. Spectrosc., 1990, 44, 1176
			up to 1.3	
Planar cathode	30 mT on cat (plasm Cathode	Anode	up to 1.5	Chen <i>et al.</i> <i>SAB</i> 1997, <b>52</b> , 1161
			up to 1.8	
Grimm	10 mT on cathode surface (sample backside)	Al I – 396.2 nm	up to 1.5	Alberts <i>et al.</i> JAAS, 2010, <b>25</b> , 1247
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### **Configurations**



Magnetic field parallel to the sample surface



Magnetic field perpendicular to the sample surface

Type of magnet	Magnetic field	Properties	T. Curie (°C)
Ferrite	low	Brittle, cheap	300
AlNiCo	medium	Brittle, expensive	540
Nd-Fe-B	high	Tough, medium price	140
Sm-Co	high	Tough, expensive	300

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Sm-Co	high	Tough, expensive	300



Type of	N° of	Magnetic
magnets	magnets	field (mT)
	2x1	20
Ferrite	2x2	30
	2x3	38
Nd-Fe-B	2x1	40

Magnetic field parallel to the sample surface



# The magnetic field depends on the sample thickness



Magnetic field parallel to the sample surface



Similar configuration but the magnetic field is independent of the sample thickness











Similar configuration but the magnetic field is independent of the sample thickness





Magnetic field parallel to the sample surface



$$R = \frac{\sqrt{2 \cdot E \cdot m}}{q \cdot B}$$

E: electron energy m: electron mass q: charge B: magnetic field



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An electromagnet could be used

Higher magnetic fields can be achieved
 Magnetic field can be regulated by the electrical current in the coil





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### Effect of the pressure and applied power





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### **Calibration and limit of detection**

#### aluminum matrix set of samples with variable copper content

<b>Reference Material</b>	Cu (mass %)	Al (mass%)
VAW E-2/8	0.20	96.21
VAW 3015-4	0.62	83.80
VAW3035-3	1.98	84.90
VAW E-3/8	4.00	84.28



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### **Depth resolution**

Sample BSH8: Ni (41.8%), Fe(14.6%), Cr (29.4%)



GD Parameters: 300 Pa - 50 W	B= 0 mT	B= 7.5 mT
Sputtering time (s)	224	226
Crater volumen (x10 <sup>7</sup> µm <sup>3</sup> )	8.1±0.3	10.1±0.4
Sputtering rate (µg/s)	3.3±0.5	3.9±9.6

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### **Depth resolution**

Sample: Ni (12.9 μm)/brass



#### Bibliographic data: WO2009130424 (A1) - 2009-10-29

★ In my patents list > EP Register II Report data error

#### MAGNETRON SOURCE FOR A GLOW DISCHARGE SPECTROMETER

Page bookmark	WO2009130424 (A1) - MAGNETRON SOURCE FOR A GLOW DISCHARGE SPECTROMETER
Inventor(s):	GANCIU-PETCU MIHAI [RO]; DIPLASU CONSTANTIN [RO]; SURMEIAN AGAVNI [RO]; GROZA ANDREEA-LILIANA [RO]; TEMPEZ AGNES [FR]; CHAPON PATRICK [FR]; CASARES MARCO [FR]; ROGERIEUX OLIVIER [FR] $\pm$
Applicant(s):	Horiba Jobin Yvon Sas [FR]; nat inst of lasers plasma and [Ro]; ganciu-petcu mihai [Ro]; Diplasu constantin [Ro]; surmeian agavni [Ro]; groza andreea-liliana [Ro]; tempez agnes [FR]; chapon patrick [FR]; casares marco [FR]; rogerieux olivier [FR] <u>+</u>





#### (12) United States Patent Ganciu-Petcu et al.

#### (54) DISCHARGE LAMP FOR GDS WITH AN AXIAL MAGNETIC FIELD

- (75) Inventors: Mihai Ganciu-Petcu, Bucarest (RO);
   Virgil Mircea Udrea, Bucarest (RO);
   Agnes Tempez, Massy (FR); Patrick Chapon, Villebon sur Yvette (FR)
- (73) Assignce: Horiba Jobin Yvon SAS, Longjumeau (FR)





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## **Conclusions**

□ The application of a magnetic field can increase the plasma emission. The magnetic field should be higher than a threshold to obtain noticeable enhancements

□ Depending on the magnet configuration, the resulting magnetic field can be parallel or perpendicular to the sample surface.

□ Depending on the magnets placement the value of the magnetic field on the plasma site can depend on the sample thickness

□ Limits of detection an order of magnitude lower than those obtained without magnetic field can be achieved. Elements not detected in absence of magnetic field can be observed by applying an appropriate magnetic field

□ It is possible to use lower pressures and powers which results extremely convenient for the analysis of polymers and organic samples.

## **Acknowledgments**

 Financial support from the Ministry of Economy and Competitiveness and the Principality of Asturias through the research projects CTQ2013-49032-C2-2-R and GRUPIN14-040

> Horiba

# Thank you for your attention!



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## **Results: pulsed rf-GD-OES**



Flow rate: 300 sccm Applied power: 80 W



#### The magnetic field affects the emission when electrons are present in the plasma

### **Results: non pulsed rf-GD-OES**



Background level is not affected by the magnetic field



 ${\bf x}$  2.17: señal iónica del aluminio (m/z = 27) adquirido en el equipo rf-GD-TOFMS a unas ndiciones de 400 Pa de presión y 40 W de potencia, en presencia de diferentes campos ticos. Para facilitar la interpretación del gráfico se incluye una vista ampliada de la región l<br/>rada. Se indica la zona en la que se han calculado los factores de incremento respecto a la intensidad registrada en ausencia de campo así como dichos factores.



Figure 9.90 espectros de masos con y sin campo en la región del plomo: espectro adquirido en

#### Alumina layer on Aluminum



The sputtering rate seems to be higher at the higher magnetic field employed The depth resolution seems worse when the magnetic field is applied but the experimental parameters selected are the optimum for the analysis without magnetic field